## NEC

# NPN SILICON POWER TRANSISTOR 2SD882

### **DESCRIPTION**

The 2SD882 is NPN silicon transistor suited for the output stage of 3 watts audio amplifier, voltage regulator, DC-DC converter and relay driver.

### **FEATURES**

• Low saturation voltage.

 $V_{CE(sat)} \le 0.5 \text{ V} (@ I_C = 2 \text{ A}, I_B = 0.2 \text{ A})$ 

Excellent h<sub>FE</sub> linearity and high h<sub>FE</sub>.

 $h_{FE}$ : 60 to 400 (@  $V_{CE}$  = 2 V,  $I_{C}$  = 1 A)

 Less cramping space required due to small and thin package and reducing the trouble for attachment to a radiator.

No insulator bushing required.

### ABSOLUTE MAXIMUM RATINGS

Maximum Temperatures		
Storage Temperature	o +15	0 °C
Junction Temperature 150 °C	Maxir	num
Maximum Power Dissipations		
Total Power Dissipation ( $T_a = 25$ °C)	1	.0 W
Total Power Dissipation ( $T_c = 25$ °C)	'	10 W
Maximum Voltages and Currents (T <sub>a</sub> = 25 °C)		
V <sub>CBO</sub> Collector to Base Voltage	40	V
V <sub>CEO</sub> Collector to Emitter Voltage	30	٧
V <sub>EBO</sub> Emitter to Base Voltage	5.0	٧
I <sub>C(DC)</sub> Collector Current (D.C)	3.0	Α
I <sub>C(pulse)</sub> * Collector Current (pulse)	7.0	Α

<sup>\*</sup>Pulse Test PW  $\leq$  350  $\mu$ s, Duty Cycle  $\leq$  2 %

# PACKAGE DIMENSIONS in millimeters (inches) 8.5 MAX. (0.334 MAX.) (0.110 MAX.) (0.047) (0.047) (0.047) (0.090) (0.090) (0.090) 1. Emitter 2. Collector connected to mounting plane 3. Base

### ELECTRICAL CHARACTERISTICS (Ta = 25 °C)

SYMBOL	CHARACTERISTIC	MIN.	TYP.	MAX.	UNIT	TEST CONDITIONS
hee1	DC Current Gain	30	150			V <sub>CE</sub> = 2.0 V, I <sub>C</sub> = 20 mA**
hEE2	DC Current Gain	60	160	400		$V_{CE} = 2.0 \text{ V}, I_{C} = 1.0 \text{ A**}$
f <sub>T</sub>	Gain Bandwidth Product		90		MHz	$V_{CE} = 5.0 \text{ V, I}_{C} = 0.1 \text{ A}$
C <sub>ob</sub>	Output Capacitance		45		рF	$V_{CB} = 10 \text{ V}, I_E = 0, f = 1.0 \text{ MHz}$
_	Collector Cutoff Current			1.0	μΑ	$V_{CB} = 30 \text{ V, I}_{E} = 0$
CBO	Emitter Cutoff Current			1.0	μΑ	$V_{EB} = 3.0 \text{ V, } I_{C} = 0$
IEBO	Collector Saturation Voltage		0.3	0.5	V	$I_C = 2.0 \text{ A}, I_B = 0.2 \text{ A**}$
V <sub>CE(sat)</sub>	Base Saturation Voltage		1.0	2.0	٧	I <sub>C</sub> = 2.0 A, I <sub>B</sub> = 0.2 A**

<sup>\*\*</sup>Pulse Test : PW  $\leq$  350  $\mu$ s, Duty Cycle  $\leq$  2 %

### Classification of h FE

Rank	R	a	Р	E
Range	60 to 120	100 to 200	160 to 320	200 to 400

Test Conditions :  $V_{CE} = 2.0 \text{ V, } I_{C} = 1.0 \text{ A}$ 

### TYPICAL CHARACTERISTICS (Ta = 25 °C)

















